

AMENDMENTS TO THE CLAIMS

1. – 27. (canceled)
28. (previously presented) A bonded structure comprising:
a first substrate;
a first electrode formed on the first substrate;
a first low-melting-point material formed on the first electrode; and
an organic binder formed on the first low-melting-point material, the organic binder including a conductive filler, wherein at least a part of the conductive filler is present within the first low-melting-point material.
29. (previously presented) The bonding structure according to claim 28 further comprising:
a second substrate;
a second electrode formed on the second substrate;
a second low-melting-point material formed on the second electrode and connected to the organic binder, wherein at least a part of the conductive filler is present within the second low-melting-point material.
30. (currently amended) A The bonding structure according to claim 28, comprising:
a first substrate;
a first electrode formed on the first substrate;
a first low-melting-point material formed on the first electrode; and
an organic binder formed on the first low-melting-point material, the organic binder including a conductive filler, wherein at least a part of the conductive filler is present within the first low-melting-point material, and wherein the first low-melting-point material comprises a Sn-Pb alloy.

31. (currently amended) A The bonding structure according to claim 29, comprising:
a first substrate;
a first electrode formed on the first substrate;
a first low-melting-point material formed on the first electrode;
an organic binder formed on the first low-melting-point material, the organic binder including a conductive filler, wherein at least a part of the conductive filler is present within the first low-melting-point material;
a second substrate;
a second electrode formed on the second substrate;
a second low-melting-point material formed on the second electrode and connected to the organic binder, wherein at least a part of the conductive filler is present within the second low-melting-point material, and
wherein the first and second low-melting-point material comprise a Sn-Pb alloy.

32. (previously presented) The bonding structure according to claim 28, wherein the conductive filler includes Ag.

33. (previously presented) The bonding structure according to claim 29, wherein the conductive filler comprises Ag.

34. (currently amended) A The bonding structure according to claim 28, comprising:
a first substrate;
a first electrode formed on the first substrate;
a first low-melting-point material formed on the first electrode; and
an organic binder formed on the first low-melting-point material, the organic binder including a conductive filler, wherein at least a part of the conductive filler is present

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within the first low-melting-point material, and wherein the conductive filler comprises solder particles.